

Tatsushi Hamaguchi

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1910278/publications.pdf>

Version: 2024-02-01

22
papers

527
citations

840776

11
h-index

888059

17
g-index

22
all docs

22
docs citations

22
times ranked

322
citing authors

#	ARTICLE	IF	CITATIONS
1	High-Power (over 100 mW) Green Laser Diodes on Semipolar $\{20\alpha\{2\}1\}$ GaN Substrates Operating at Wavelengths beyond 530 nm. Applied Physics Express, 2012, 5, 082102.	2.4	110
2	Room-temperature continuous-wave operation of GaN-based vertical-cavity surface-emitting lasers fabricated using epitaxial lateral overgrowth. Applied Physics Express, 2015, 8, 062702.	2.4	75
3	Milliwatt-class GaN-based blue vertical-cavity surface-emitting lasers fabricated by epitaxial lateral overgrowth. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1170-1176.	1.8	65
4	Lateral optical confinement of GaN-based VCSEL using an atomically smooth monolithic curved mirror. Scientific Reports, 2018, 8, 10350.	3.3	51
5	Long-Lifetime True Green Laser Diodes with Output Power over 50 mW above 525 nm Grown on Semipolar $\{20\alpha\{2\}1\}$ GaN Substrates. Applied Physics Express, 2012, 5, 082103.	2.4	43
6	A review on the latest progress of visible GaN-based VCSELs with lateral confinement by curved dielectric DBR reflector and boron ion implantation. Japanese Journal of Applied Physics, 2019, 58, SC0806.	1.5	36
7	Sub-milliampere-threshold continuous wave operation of GaN-based vertical-cavity surface-emitting laser with lateral optical confinement by curved mirror. Applied Physics Express, 2019, 12, 044004.	2.4	30
8	Room-temperature continuous-wave operation of green vertical-cavity surface-emitting lasers with a curved mirror fabricated on $\{20\alpha\{2\}1\}$ semi-polar GaN. Applied Physics Express, 2020, 13, 041002.	2.4	27
9	Lateral carrier confinement of GaN-based vertical-cavity surface-emitting diodes using boron ion implantation. Japanese Journal of Applied Physics, 2016, 55, 122101.	1.5	26
10	Single transverse mode operation of GaN-based vertical-cavity surface-emitting laser with monolithically incorporated curved mirror. Applied Physics Express, 2019, 12, 084003.	2.4	25
11	GaN-based Vertical-Cavity Surface-Emitting Lasers Incorporating Dielectric Distributed Bragg Reflectors. Applied Sciences (Switzerland), 2019, 9, 733.	2.5	15
12	Narrow Emission of Blue GaN-Based Vertical-Cavity Surface-Emitting Lasers With a Curved Mirror. IEEE Photonics Journal, 2022, 14, 1-5.	2.0	6
13	Longitudinal mode control in long cavity VCSELs with a curved mirror. Applied Physics Express, 2022, 15, 072009.	2.4	5
14	Impact of oxygen on band structure at the Ni/GaN interface revealed by hard X-ray photoelectron spectroscopy. Applied Physics Letters, 2021, 118, 121603.	3.3	4
15	Continuous wave operation of high power GaN-based blue vertical-cavity surface-emitting lasers using epitaxial lateral overgrowth. Proceedings of SPIE, 2016, , .	0.8	3
16	49 th Invited Paper: Blue and Green VCSEL for Full-Color Display. Digest of Technical Papers SID International Symposium, 2021, 52, 677-679.	0.3	2
17	Narrow emission of blue GaN-based vertical-cavity surface-emitting lasers with a curved mirror. , 2021, , .		2
18	Narrow Divergence Emission from Blue GaN-based VCSELs with Curved Mirror. IEEE Transactions on Electronics, Information and Systems, 2021, 141, 1281-1285.	0.2	1

#	ARTICLE	IF	CITATIONS
19	Mode control in long cavity VCSELs with a curved mirror. , 2022, , .		1
20	Incorporation of a Curved Mirror into GaN-Based VCSEL. , 2018, , .		0
21	Recent progress in GaN-based Vertical-Cavity Surface-Emitting Lasers Having Dielectric Distributed Bragg Reflectors. , 2018, , .		0
22	Recent progress in GaN-based vertical-cavity surface-emitting lasers with lateral optical confinement due to an incorporated curved mirror. , 2019, , .		0